

1 **First-principles calculation of scattering potentials of Si-Ge and**
2 **Sn-Ge dimers on Ge(001) surfaces**

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5 (Dated: November 2, 2012)

Abstract

The scattering potential of the defects on Ge(001) surfaces is investigated by first-principles methods. The standing wave in the spatial map of the local density of states obtained by wave function matching is compared to the image of the differential conductance measured by scanning tunneling spectroscopy. The period of the standing wave and its phase shift agree with those in the experiment. It is found that the scattering potential becomes a barrier when the electronegativity of the upper atom of the dimer is larger than that of the lower atom, while it acts as a well in the opposite case.

6 PACS numbers: 73.20.Hb, 72.10.Fk, 82.20.Wt

7 With the progress of new techniques for the atomic-scale manipulation and modification
8 of materials, there is considerable interest in the electron scattering properties of nanos-
9 tructures both experimentally and theoretically. Scanning tunneling microscopy (STM) [1]
10 and mechanically controllable break junctions [2] have been extensively used to study the
11 conductance of atomic-scale systems suspended between two electrodes so far, and today it
12 is already well known that the conductance of a single strand of atomic wire is quantized in
13 the unit of $2e^2/h$, where e is the electron charge and h is Planck's constant [3]. Although
14 these techniques are powerful tools to understand electron transport phenomena of such
15 minute systems, it has not been easy to discuss the contribution of local chemical bonds
16 to the electron scattering because these techniques only measure the current between two
17 electrodes with an applied bias voltage. On the other hand, the spatial maps of the local
18 density of states (LDOS) obtained by scanning tunneling spectroscopy (STS) can provide
19 the images of standing waves, which give important information about the dispersion rela-
20 tion of surface states [4, 5] as well as about the electron scattering process at the potential
21 barrier [4].

22 Tomatsu *et al.* demonstrated the standing wave around oppositely buckled Ge dimers
23 on a Ge(001) surface and discussed the difference in scattering potential between the Si-
24 Ge and Sn-Ge dimers [6, 7]. They also carried out first-principles calculations based on
25 the density functional theory (DFT) [8] using periodic supercells to identify the surface
26 atomic and electronic structures observed in STM images and STS spectra. However, the
27 standing waves emerge as a result of the difference in the coefficients between incident and
28 reflected waves of scattering wave functions, which cannot be calculated by models under
29 periodic boundary conditions along the scattering direction. Thus, it is not straightforward
30 to determine the scattering potential using the periodic models.

31 The scattering properties of atomic-scale structures are studied by DFT calculations
32 combined with nonequilibrium Green's functions [9] or wave function matching methods [10–
33 12]. In these approaches, the scatterers are sandwiched between electrodes that extended
34 semi-infinitely and are connected to bulks; thus, wave functions extending over the entire
35 system can be correctly described as a scattering state distributed as a result of the existence
36 of scatterers when an electron comes from infinitely deep inside the electrode. Although these
37 approaches have been used to investigate the transport properties of atoms, molecules, and
38 thin films suspended by two electrodes so as to model the experiments using the STM and

mechanically controllable break junctions, to the best of my knowledge, no studies have attempted to obtain an understanding of the relationship between local chemical bonds and their scattering properties by examining the scattering potential in first-principles transport calculations.

In this Letter, I apply the first-principles transport calculation to the investigation of the standing waves due to scattering at Si-Ge and Sn-Ge dimers on a Ge(001) surface. The real-space procedure of the DFT calculation combined with the overbridging-boundary matching (OBM) method provides the reflection and transmission coefficients of the incident electrons, which enable us to determine the scattering potential and the phase shift of the standing waves. The calculated phase shift of the standing waves is in good agreement with that measured in experiments [7]. The defects act as a barrier when a Si (Sn) atom exists at the lower (upper) position of the dimer, while they behave as a well in the case of the other way around. It is found that the scattering potential is related to the stabilization of the π bands of the Ge(001) surface due to the Jahn-Teller effect of the dimers and the difference in electronegativity between Ge and the impurity atom.

The first-principles calculation method used here to obtain the electron scattering properties is based on the real-space finite-difference approach [12–14], which enables us to determine the self-consistent electronic ground state with a high degree of accuracy by a timesaving double-grid technique [12, 14]. Moreover, the real-space calculations eliminate the serious drawbacks of the conventional plane-wave approach, such as its inability to describe nonperiodic systems accurately. The scattering properties of Ge-Si and Ge-Sn dimers on a Ge(001) surface suspended between Ge(001)-(2 $\times$ 2) surfaces are examined by making use of this advantage of the combination of the real-space finite-difference approach and the OBM method [11, 12].

Figure 1 shows the computational model, where the scattering region is connected to the Ge(001)-(2 $\times$ 2) surfaces. The scattering region consists of six Ge atom layers with a (2 $\times$ 6) lateral cell, and the topmost atoms are buckled so as to form a surface reconstructed structure, while the bottommost layers are terminated by hydrogen atoms. The dimensions of the cells are $L_x = 23.92$ Å, $L_y = 7.97$ Å, and $L_z = 17.94$ Å for the scattering region, and $L_x = 7.97$ Å, $L_y = 7.97$ Å, and $L_z = 17.94$ Å for the Ge(001)-(2 $\times$ 2) surface electrode region, where L_x and L_y are the lengths in the x - and y -directions parallel to the surface, respectively, and L_z is the length in the z -direction. The Ge-Ge dimer at the center of the

71 scattering region is replaced by Ge-Si or Ge-Sn dimer as a defect. When the Si and Ge atoms
72 are located at the lower and upper sides of the dimer, respectively, the dimer is referred as
73 an SiL dimer. Other dimers are named in a similar manner. During the optimization of
74 the atomic configurations in both the electrode and scattering regions, all atoms except
75 for those in the bottommost layers are relaxed until all the force components drop below
76 0.05 eV/Å by imposing the periodic boundary condition in the x -, y -, and z -directions.
77 The grid spacing is set at ~ 0.20 Å and k -space integrations are performed with $4 \times 4\mathbf{k}$
78 points in the irreducible wedge of a two-dimensional Brillouin zone of the Ge(001)-(2 $\times$ 2)
79 surface. Exchange correlation effects are treated by a local density approximation [15] of the
80 DFT, and the projector augmented wave method [16] is used to describe the electron-ion
81 interaction.

82 In the OBM calculation performed to obtain the scattering wave functions, the norm-
83 conserving pseudopotentials [17] of Troullier and Martins [18] are employed instead of the
84 projector augmented wave method. To determine the Kohn-Sham effective potential, a
85 supercell is used under a periodic boundary condition, and then the scattering wave functions
86 are computed under the semi-infinite boundary condition obtained non-self-consistently. It
87 has been reported that this procedure is just as accurate in the linear response regime but
88 significantly more efficient than performing computations self-consistently on a scattering-
89 wave basis [19].

90 Figure 2 shows the charge density distribution of the scattering wave functions for the
91 electrons propagating from both the left and right electrodes with an energy of $E_F + 0.55$ eV,
92 which corresponds to the spatial image of the differential conductance in the STS spectrum
93 [7]. Here, E_F is the Fermi energy. The standing waves on the xy plane, which is 2.7 Å
94 from the upper Ge atom of the Ge(001) surface, are plotted. It is found that the standing
95 wave emerges in all the models. Since the π^* band of the Ge(001)-(2 $\times$ 2) surface crosses the
96 energy of $E_F + 0.55$ eV at $k_x = 0.454 \times \pi/L_x$, the period of the standing waves is $2k_x$ (=17.6
97 Å), which is slightly shorter than that observed in the experiment (~ 22 Å). Taking into
98 account the fact that the local density approximation underestimates the energy band gap
99 and that the period of the standing wave decreases as the sample bias increases in the spatial
100 image of the STS spectrum in Ref. 7, these results agree with those of the experiments.

101 The line profiles of the standing waves along the dimer row including the impurity atom
102 are depicted in Fig. 3. To demonstrate the period and phase shift of the standing waves

clearly, the amplitude of the waves is fitted by

$$\alpha(x) = A \cos(2k_x + \phi), \quad (1)$$

where A and ϕ are the amplitude and phase shift of the standing waves, respectively. The fitting is carried out using the amplitude of the standing waves on the upper atom of the dimer (indicated by “•” in Fig. 2). Table I shows the amplitude and phase shift of the standing waves. The amplitude of the SnL (SiU) dimer is larger (smaller) than that of the SiL dimer, and the phase shifts of the SiU and SnL dimers are negative, while that of the SiL dimer is positive. These findings consistent with experimental results [7].

Let us discuss the scattering property of the defects in more detail. The OBM method provides the reflection coefficients of the scattering waves, which give us information on the scattering potential upon using a one-dimensional free-electron-like model. Table II shows the calculated reflection coefficients and the reflection probabilities. The barrier height V and length a of the scattering potential are determined by

$$c^{ref} = \frac{(k^2 - K^2)(1 - e^{4iKa})e^{2ika}}{(k + K)^2 - (k - K)^2e^{4iKa}}, \quad (2)$$

which is derived from the penetration of electrons into a one-dimensional square potential barrier on the basis of quantum mechanics. Here, $k = v/\hbar$ and $K = \sqrt{(v^2 - 2mV)/\hbar}$, where $\hbar$ is the reduced Planck’s constant, m is the electron mass, and v is the group velocity of the incident wave. V and a are fit so that the reflection coefficients correspond to those obtained by the OBM method. The calculated V and a are shown in Table II. The SiU and SnL dimers behave as a potential barrier, whereas the SiL and SnU dimers behave as a potential well. The signs of the scattering potential height except for that of the SnU dimer agree with those reported by Tomatsu *et al.* [7], where the potentials are estimated by fitting the line profile of the STS spectrum and/or by DFT calculation using periodic supercells. However, the potential of the SnU dimer, which is not observed in the experiment, is not in agreement.

It is known that an electron conducts through the π^* band of the Ge-Ge dimer on the Ge(001) surface. According to the explanation by Haneman [20], the sp^3 bonding state is stabilized as the bond angle around the atom of the dimer decreases. In the case of a Ge(001) surface, the π band accumulating around the upper atom of the dimer is occupied after the surface reconstruction, as shown in Fig. 4(a). When the electronegativity of the

upper atom is larger than that of the lower atom, the energy of the π (π^*) band further decreases (increases) owing to the low (high) electronegativity of the lower (upper) atom [Figs. 4(b) and 4(c)]. Since the Mulliken electronegativities of Si, Ge, and Sn are 2.0, 1.9, and 1.8, respectively, the energy of the π^* bands of the SiU and SnL dimers is higher than that of the SiL and SnU dimers [Figs. 4(b) and 4(c)]. Thus, the scattering potential of the SiU and SnL dimers acts as a barrier for the conducting electrons, whereas that of the SiL and SnU dimers acts as a well. In addition, because the electrons conduct through the states accumulating at the lower atom of the dimer, the length of the scattering potential barrier increases long when the impurity atom exists at the lower side of the dimer. In Ref. 7, the projected charge density distribution of the π band of the SiL dimer is high at the defect, while it is low in the case of the SnL dimer. Moreover, the energy gap between the π and π^* bands, $\varepsilon_{\pi^*} - \varepsilon_{\pi}$, of the SnL dimer is larger than that of the SiL dimer, which supports the explanation.

In summary, the scattering potential of the defects on Ge(001) surface is investigated by first-principles calculation. The phase shifts of the standing waves due to the defects are in agreement with those obtained by experiments [7]. By calculating the reflection coefficients of the scattering wave functions, it was found that the scattering potentials of the SiL and SnU dimers act as a well, while those of the SiU and SnL dimers behave as a barrier. This characteristic is interpreted in terms of the electronegativity of the defects; when the electronegativity of the upper site of the dimer is large, the energy gap between the π and π^* bands increases, resulting in the generation of the potential barrier for the π^* electrons. This explanation is also consistent with the LDOS in the vicinity of the dimers and with the value of $\varepsilon_{\pi^*} - \varepsilon_{\pi}$ computed using a conventional periodic supercell. In addition, the results demonstrate the applicability of first-principles transport calculations to the investigation of the scattering potential and phase shift due to defects on surfaces in collaboration with STM and STS measurements.

The author would like to thank Kota Tomatsu and Fumio Komori of the University of Tokyo for providing us the geometry of the Ge surfaces and thank Yoshitada Morikawa and Shoichiro Saito of Osaka University and Osamu Sugino of the University of Tokyo for fruitful discussion. This research was partially supported by Strategic Japanese-German Cooperative Program from Japan Science and Technology Agency and Deutsche Forschungsgemeinschaft, by the Computational Materials Science Initiative (CMSI), and by a Grant-in-Aid for

Scientific Research on Innovative Areas (Grant No. 22104007) from the Ministry of Education, Culture, Sports, Science and Technology, Japan. The numerical calculation was carried out using the computer facilities of the Institute for Solid State Physics at the University of Tokyo and Center for Computational Sciences at University of Tsukuba.

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FIGURES

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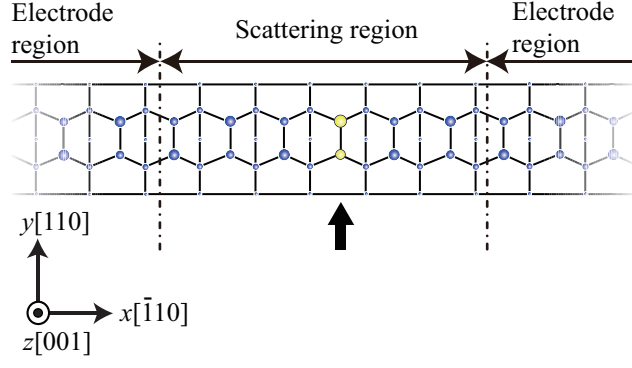


FIG. 1. Schematic image of computational model. Dark (blue) spheres are Ge atoms and light (yellow) spheres represent the dimer replaced by a Ge-Si or Ge-Sn dimer.

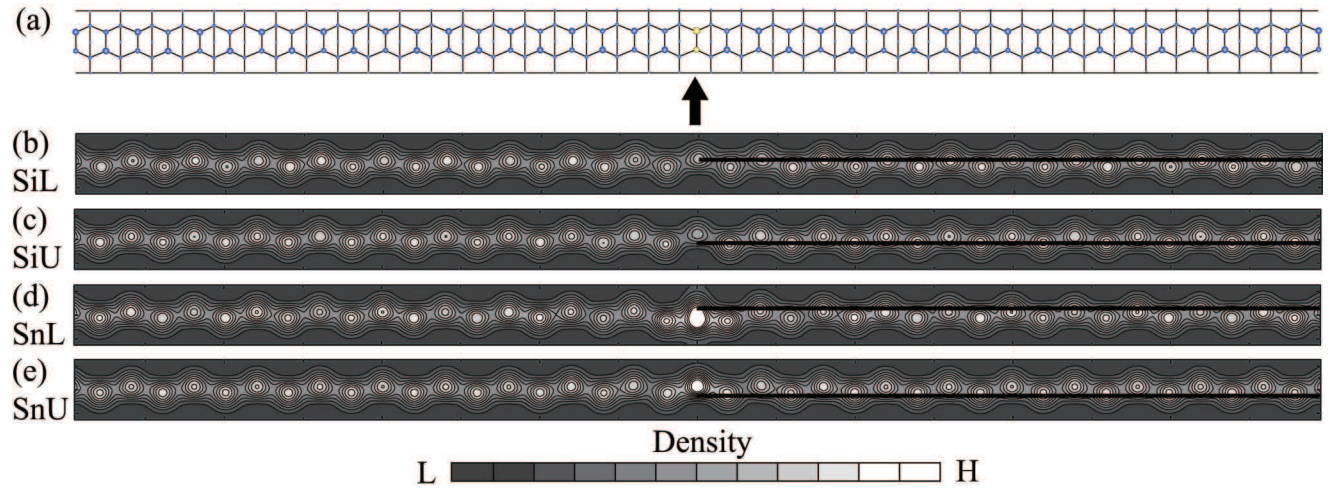


FIG. 2. Surface atomic structure (a) and spatial images of standing waves for (b) SiL, (c) SiU, (d) SnL, and (e) SnU dimers. Each contour represents a density of $0.496 \times 10^{-5} \text{ e}/\text{\AA}^3/\text{eV}/\text{spin}$ higher or lower than that of the adjacent contours.

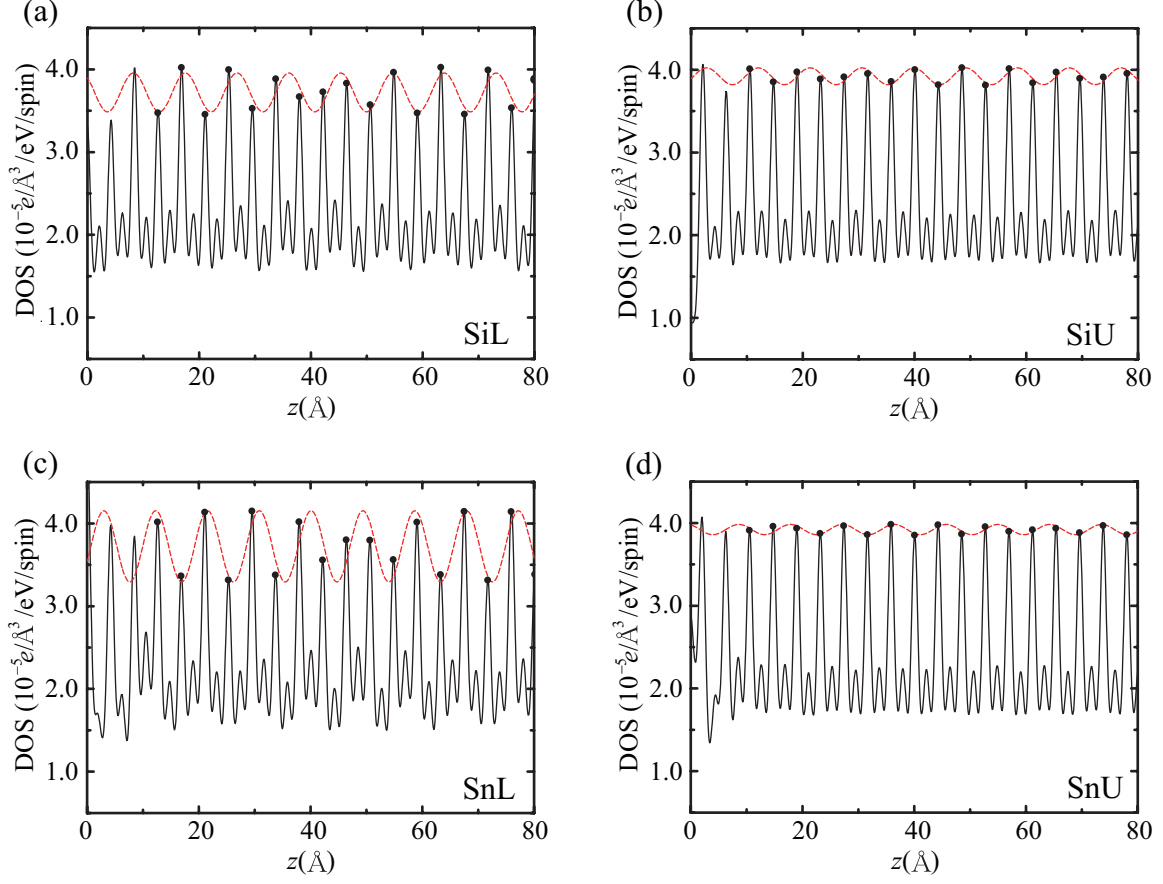


FIG. 3. Line profiles along thick solid lines in Fig. 2 for (a) SiL, (b) SiU, (c) SnL, and (d) SnU dimers. Solid and dashed curves represent the standing waves and the curves fitted by Eq. (1) using the data indicated by bullet points, respectively.

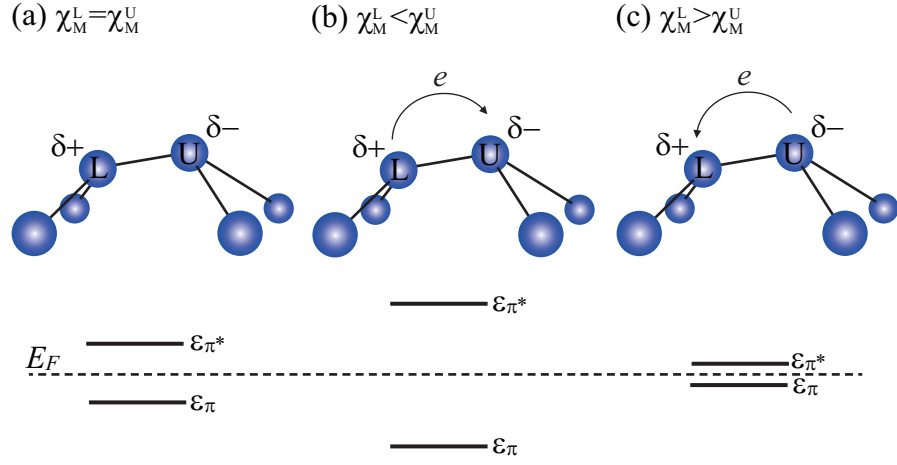


FIG. 4. Schematic image for opening the energy gap between ε_{π} and ε_{π^*} .

TABLE I. Amplitude and phase shift of the standing waves around the Ge-Si and Ge-Sn dimers.

Model	Amplitude A ($e/\text{\AA}^3/\text{eV}/\text{spin}$)	Phase shift ϕ (rad)
SiL	3.908×10^{-7}	0.221π
SiU	1.692×10^{-7}	-0.602π
SnL	7.169×10^{-7}	-0.650π
SnU	1.031×10^{-7}	0.142π

TABLE II. Reflection coefficients obtained by OBM method, barrier heights, and barrier lengths calculated from the reflection coefficients using Eq. (2).

Model	Coefficient	Height V (V)	Length a (Å)
SiL	$0.0519 + 0.0565i$	-0.801	5.203
SiU	$-0.0044 - 0.0270i$	4.444	3.518
SnL	$-0.0293 - 0.1092i$	1.394	4.858
SnU	$0.0138 + 0.0097i$	-0.152	4.378